

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

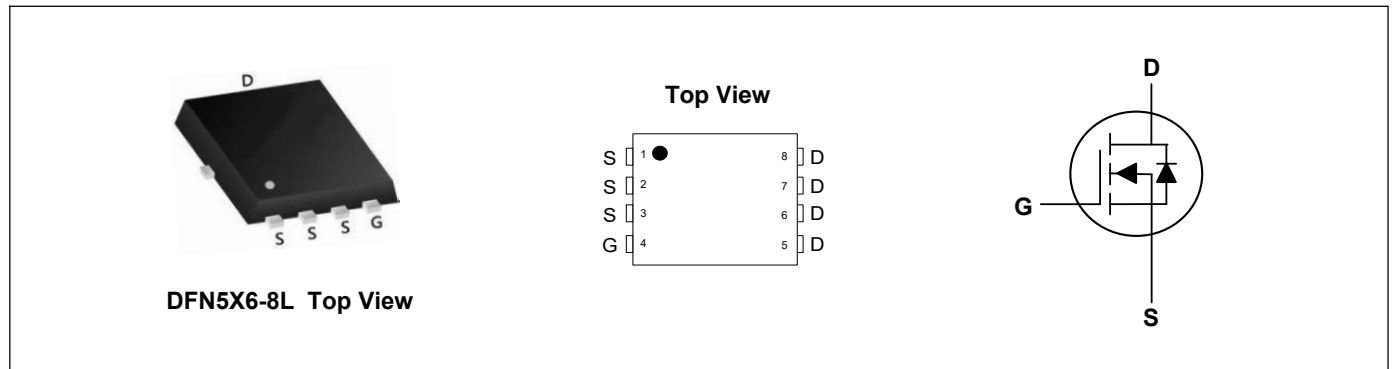
Product Summary



V_{DS}	30	V
I_D	35	A
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	7	m Ω
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	12	m Ω

Applications

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings($T_C=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	35	A
Pulsed Drain Current	I_{DM}	120	A
Single Pulse Avalanche Energy ³	EAS	150	mJ
Total Power Dissipation	P_D	40	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	3.1	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	---	---	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =12A	---	5.9	7	mΩ
		V _{GS} =4.5V, I _D =10A	---	8.9	12	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	1	1.6	3	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =12A	30	---	---	S
Total Gate Charge	Q _g	V _{DS} =15V, V _{GS} =10V, I _D =12A	---	45	---	nC
Gate-Source Charge	Q _{gs}		---	13	---	
Gate-Drain Charge	Q _{gd}		---	10	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =15V, I _D =12A, V _{GS} =10V, R _G =6Ω	---	18	---	ns
Rise Time	T _r		---	10	---	
Turn-Off Delay Time	T _{d(off)}		---	34	---	
Fall Time	T _f		---	10	---	
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	2330	---	pF
Output Capacitance	C _{oss}		---	460	---	
Reverse Transfer Capacitance	C _{rss}		---	230	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ²	I _S		---	---	35	A
Diode Forward Voltage ¹	V _{SD}	V _{GS} =0V, I _F =12A, T _J =25°C	---	0.85	1.2	V
Reverse Recovery Time	t _{rr}	I _F =I _S , di/dt=100A/μs, T _J =25°C	---	---	47	nS
Reverse Recovery Charge	Q _{rr}		---	---	25	nC

Note:

- The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- ESD condition: T_J=25°C, V_{DD}=15V, V_{GS}=10V, L=0.1mH, R_g=25Ω

Typical Characteristics

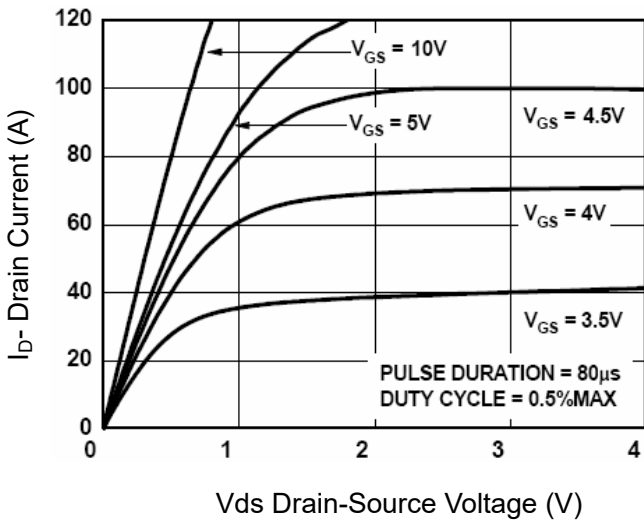


Figure 1 Output Characteristics

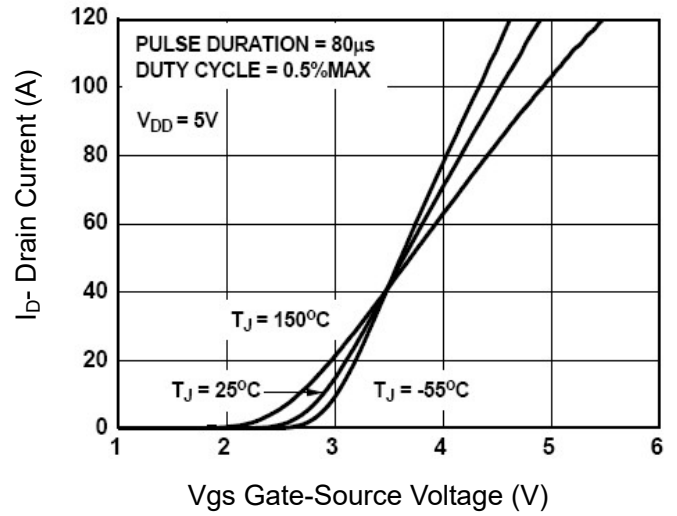


Figure 2 Transfer Characteristics

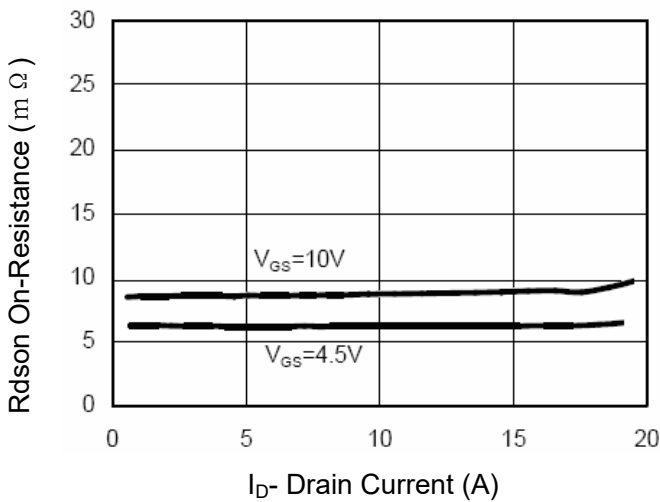


Figure 3 Rdson- Drain Current

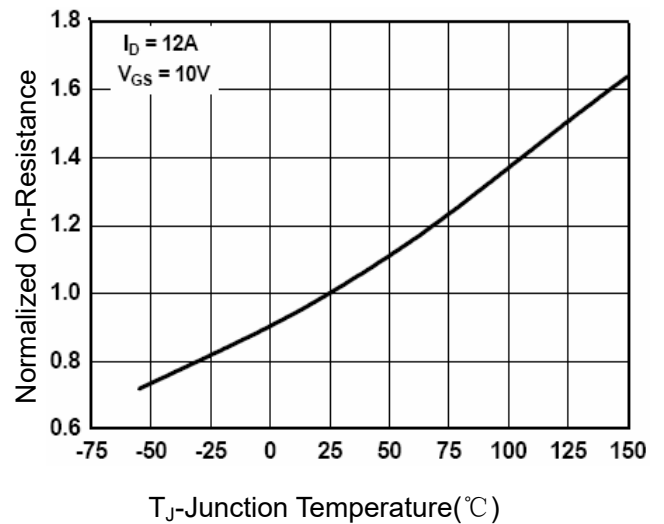


Figure 4 Rdson-Junction Temperature

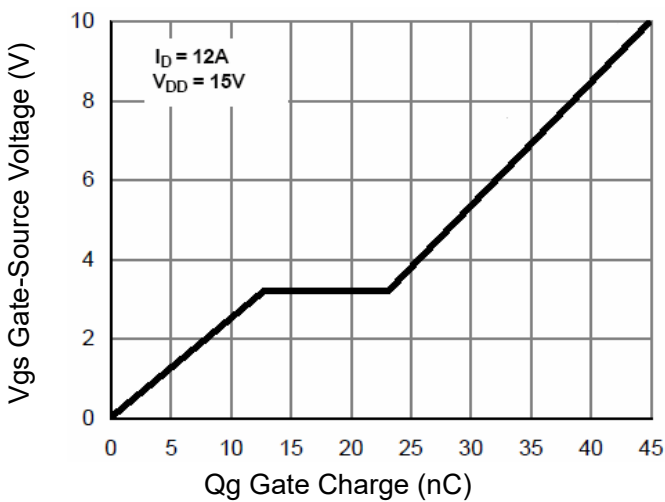


Figure 5 Gate Charge

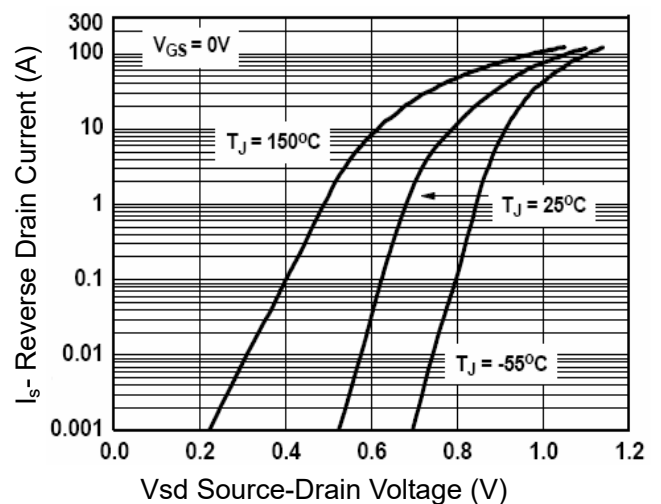


Figure 6 Source- Drain Diode Forward

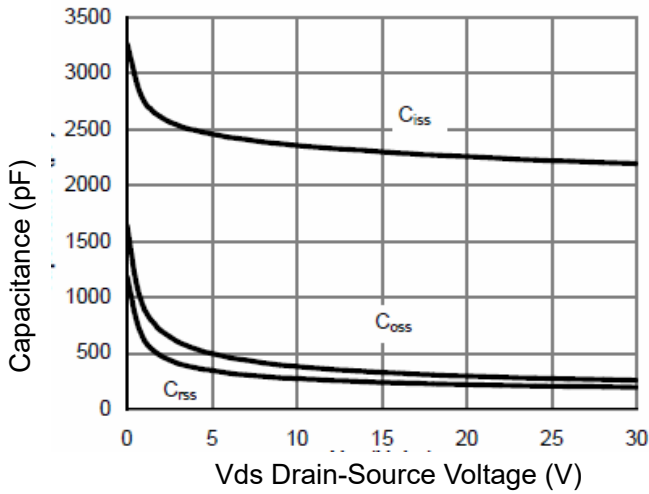


Figure 7 Capacitance vs Vds

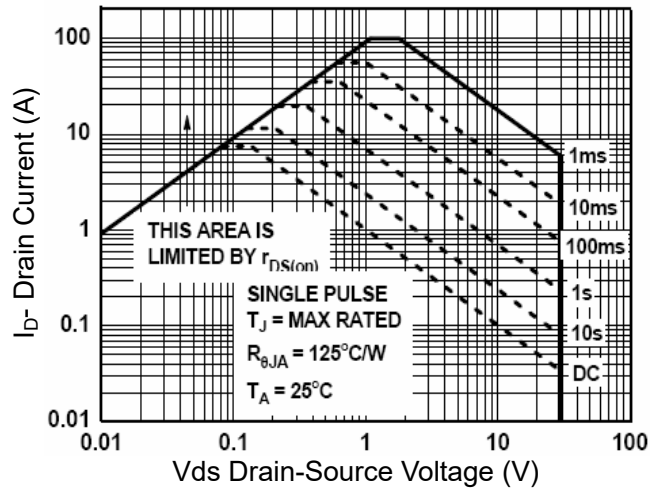


Figure 8 Safe Operation Area

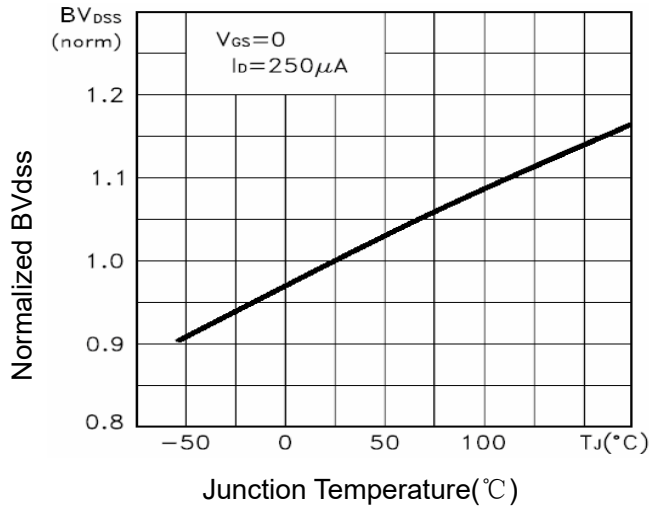


Figure 9 BV_{DSS} vs Junction Temperature

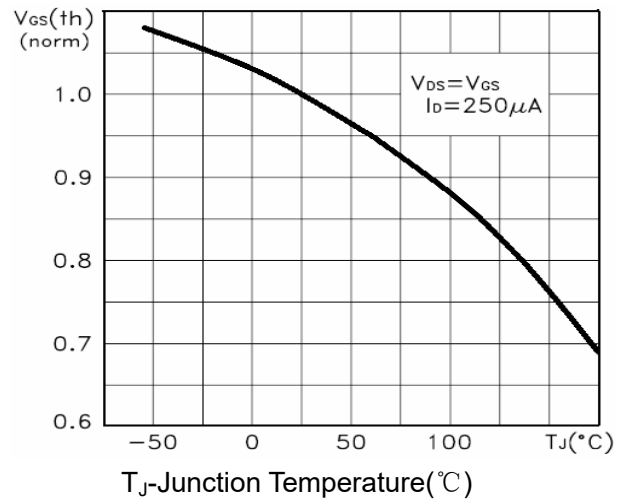


Figure 10 V_{GS(th)} vs Junction Temperature

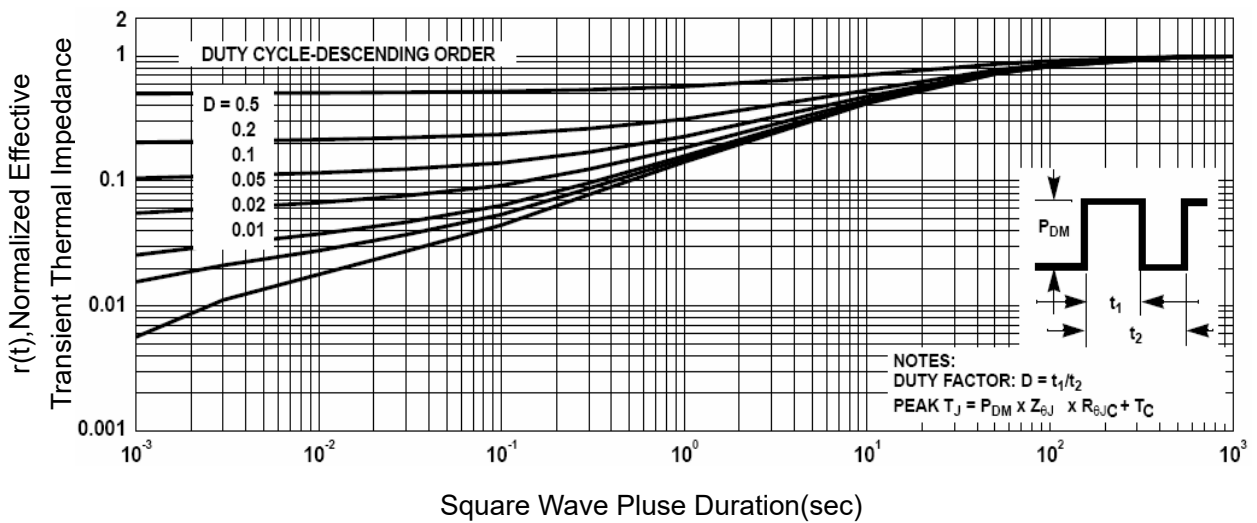
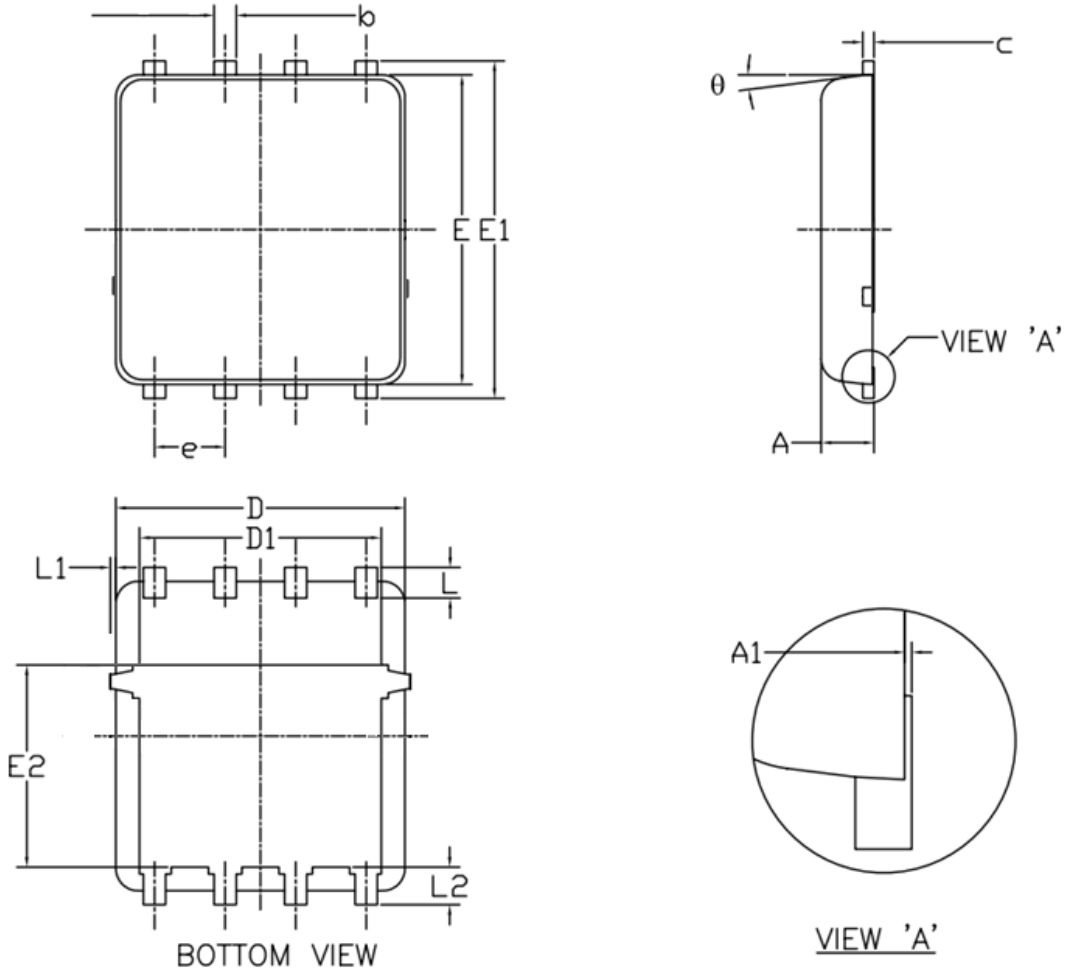


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.90	1.00	1.20	E1	5.90	6.10	6.35
A1	0.00	--	0.05	E2	3.38	3.58	3.92
b	0.30	0.40	0.51	e	1.27 BSC		
c	0.20	0.25	0.33	L	0.51	0.61	0.71
D	4.80	4.90	5.40	L1	--	--	0.15
D1	3.61	4.00	4.25	L2	0.41	0.51	0.61
E	5.65	5.80	6.06	θ	0°	--	12°